

MOSFETs Silicon N-channel MOS (U-MOSIV)

# TK18E10K3

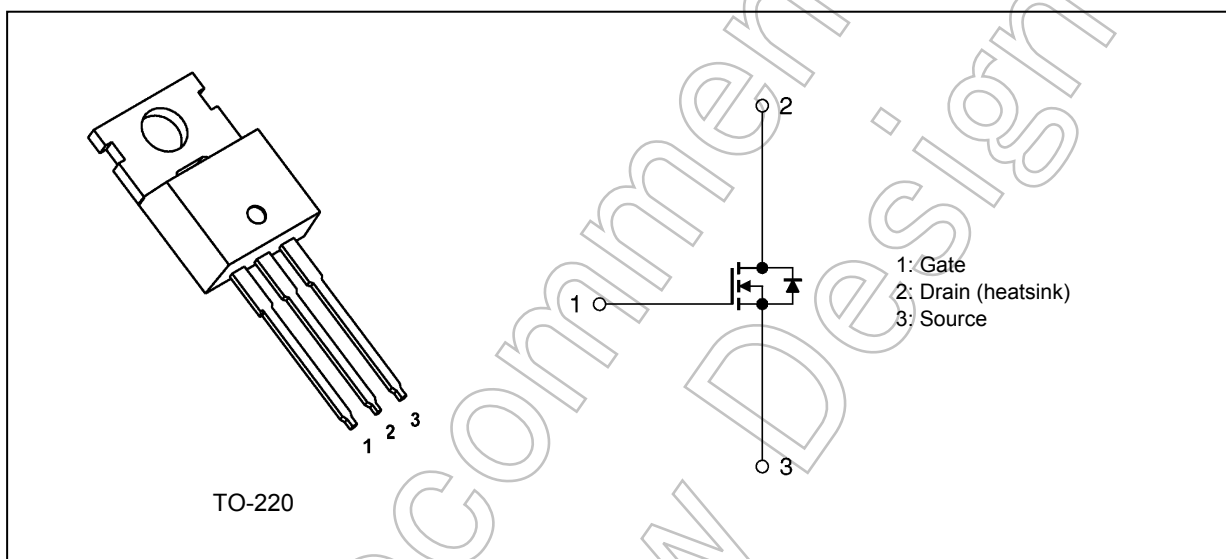
## 1. Applications

- Switching Voltage Regulators

## 2. Features

- Low drain-source on-resistance:  $R_{DS(ON)} = 33 \text{ m}\Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 28 \text{ S}$  (typ.)
- Low leakage current:  $I_{DSS} = 10 \text{ }\mu\text{A}$  (max) ( $V_{DS} = 100 \text{ V}$ )
- Enhancement mode:  $V_{th} = 2.0 \text{ to } 4.0 \text{ V}$  ( $V_{DS} = 10 \text{ V}$ ,  $I_D = 1 \text{ mA}$ )

## 3. Packaging and Internal Circuit



## 4. Absolute Maximum Ratings (Note) ( $T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	$V_{DSS}$	100	V
Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )	$V_{DGR}$	100	
Gate-source voltage	$V_{GSS}$	$\pm 20$	
Drain current (DC) (Note 1)	$I_D$	18	A
Drain current (pulsed) (Note 1)	$I_{DP}$	54	
Power dissipation ( $T_c = 25^\circ\text{C}$ )	$P_D$	71	W
Single-pulse avalanche energy (Note 2)	$E_{AS}$	28	mJ
Avalanche current	$I_{AR}$	18	A
Repetitive avalanche energy (Note 3)	$E_{AR}$	7.1	mJ
Channel temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production

2010-09

## 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	$R_{th(ch-c)}$	1.76	°C/W
Channel-to-ambient thermal resistance	$R_{th(ch-a)}$	83.3	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD} = 25\text{ V}$ ,  $T_{ch} = 25^\circ\text{C}$  (initial),  $L = 0.14\text{ mH}$ ,  $R_G = 25\ \Omega$ ,  $I_{AR} = 18\text{ A}$

Note 3: Repetitive rating; pulse width limited by maximum channel temperature

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

Not Recommended  
for New Design

## 6. Electrical Characteristics

### 6.1. Static Characteristics ( $T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$	—	—	$\pm 1$	$\mu\text{A}$
Drain cut-off current	$I_{DSS}$	$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$	—	—	10	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	100	—	—	V
Drain-source breakdown voltage	$V_{(BR)DSX}$	$I_D = 10\text{ mA}, V_{GS} = -20\text{ V}$	65	—	—	
Gate threshold voltage	$V_{th}$	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	2.0	—	4.0	
Drain-source on-resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 9\text{ A}$	—	33	42	$\text{m}\Omega$
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 9\text{ A}$	14	28	—	S

### 6.2. Dynamic Characteristics ( $T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input capacitance	$C_{iss}$	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	1580	—	pF
Reverse transfer capacitance	$C_{rss}$		—	135	—	
Output capacitance	$C_{oss}$		—	200	—	
Switching time (rise time)	$t_r$	See Figure 6.2.1.	—	9	—	ns
Switching time (turn-on time)	$t_{on}$		—	21	—	
Switching time (fall time)	$t_f$		—	7	—	
Switching time (turn-off time)	$t_{off}$		—	30	—	

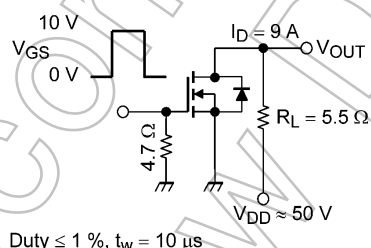


Fig. 6.2.1 Switching Time Test Circuit

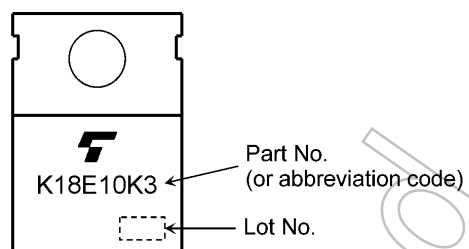
### 6.3. Gate Charge Characteristics ( $T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Total gate charge (gate-source plus gate-drain)	$Q_g$	$V_{DD} \approx 80\text{ V}, V_{GS} = 10\text{ V}, I_D = 18\text{ A}$	—	33	—	nC
Gate-source charge	$Q_{gs}$		—	20	—	
Gate-drain charge	$Q_{gd}$		—	13	—	

### 6.4. Source-Drain Characteristics ( $T_a = 25^\circ\text{C}$ unless otherwise specified)

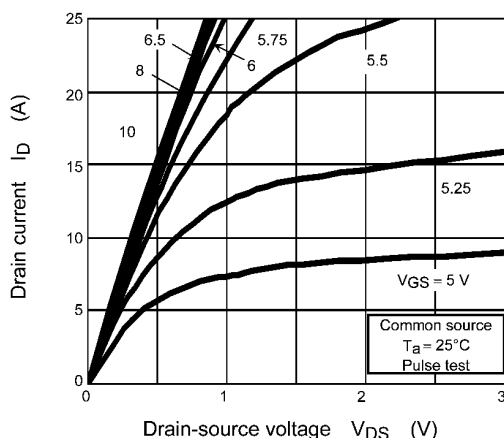
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Reverse drain current (DC) (Note 4)	$I_{DR}$	—	—	—	18	A
Reverse drain current (pulsed) (Note 4)	$I_{DRP}$	—	—	—	54	
Diode forward voltage	$V_{DSF}$	$I_{DR} = 18\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.2	V
Reverse recovery time	$t_{rr}$	$I_{DR} = 18\text{ A}, V_{GS} = 0\text{ V}$ $-dI_{DR}/dt = 50\text{ A}/\mu\text{s}$	—	53	—	ns
Reverse recovery charge	$Q_{rr}$		—	58	—	nC

Note 4: Ensure that the channel temperature does not exceed  $150^\circ\text{C}$ .

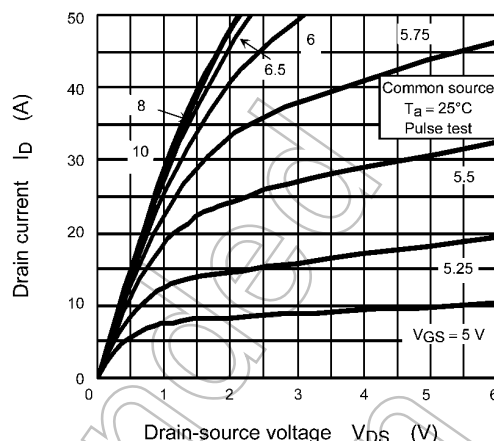
**7. Marking****Fig. 7.1 Marking**

Not Recommended  
for New Design

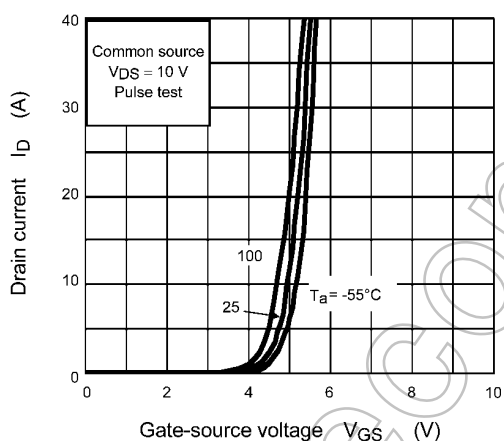
# 8. Characteristics Curves (Note)



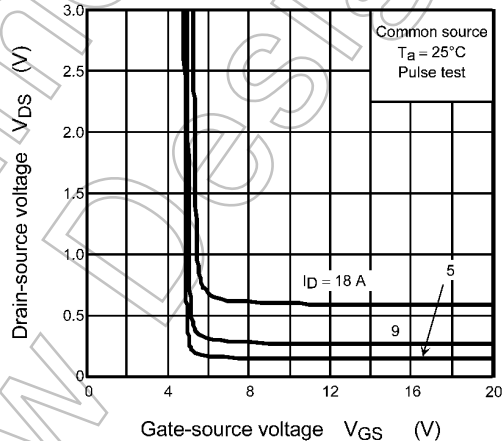
**Fig. 8.1**  $I_D - V_{DS}$



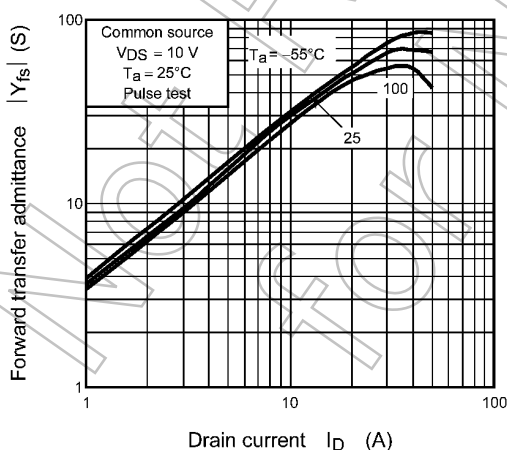
**Fig. 8.2**  $I_D - V_{DS}$



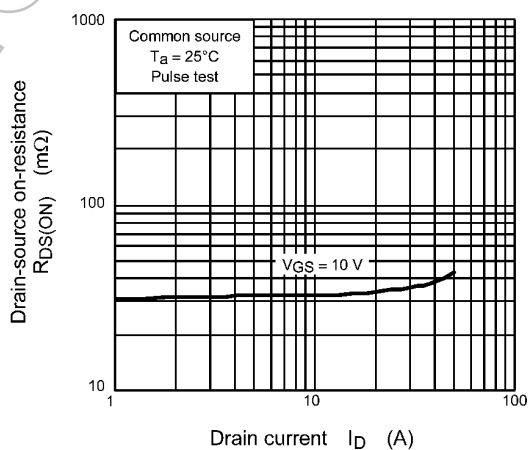
**Fig. 8.3**  $I_D - V_{GS}$



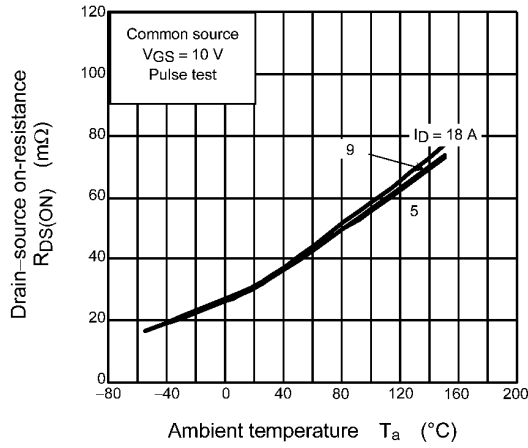
**Fig. 8.4**  $V_{DS} - V_{GS}$



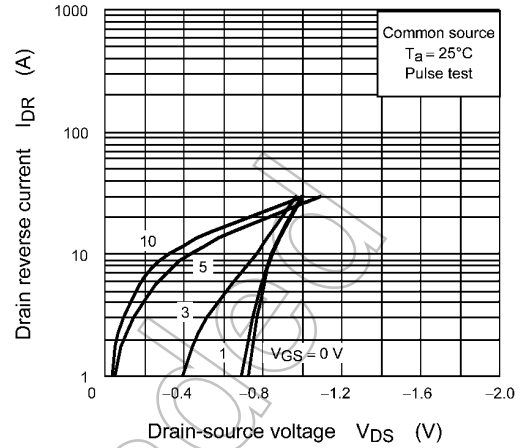
**Fig. 8.5**  $|Y_{fs}| - I_D$



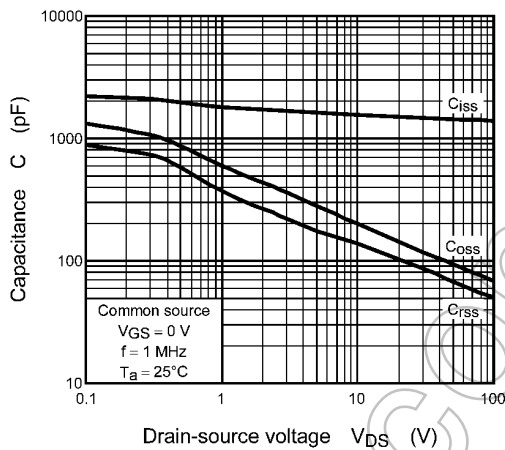
**Fig. 8.6**  $R_{DS(ON)} - I_D$



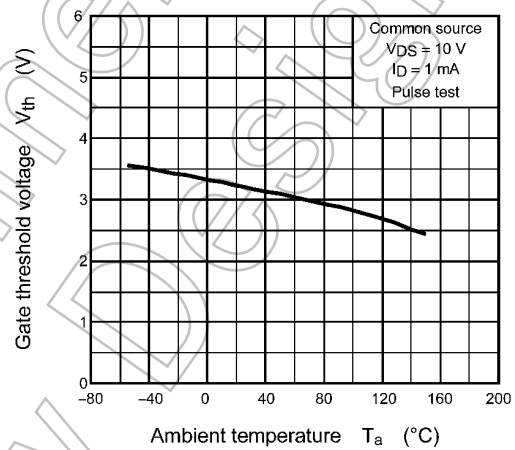
**Fig. 8.7  $R_{DS(ON)} - T_a$**



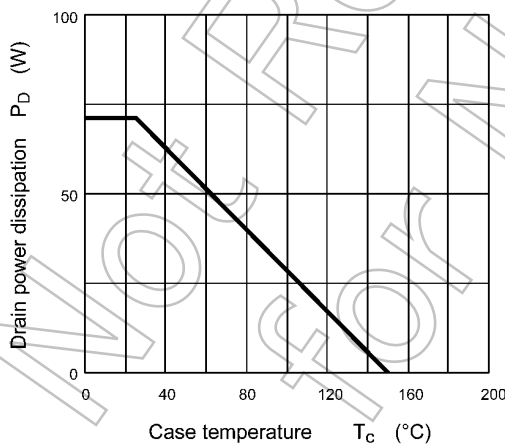
**Fig. 8.8  $I_{DR} - V_{DS}$**



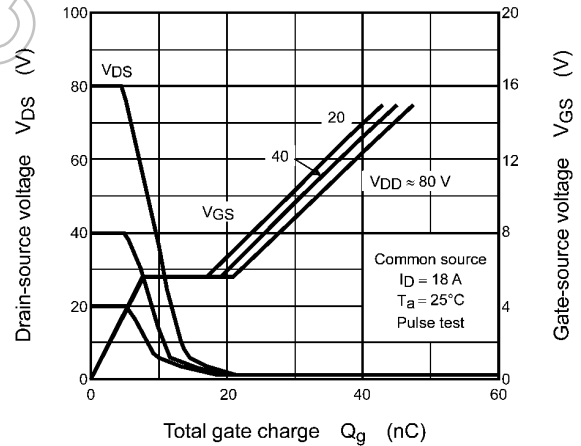
**Fig. 8.9 Capacitance -  $V_{DS}$**



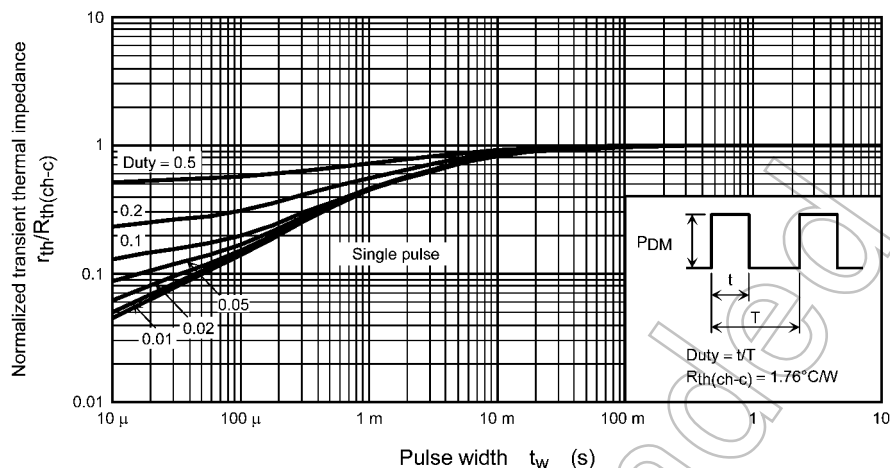
**Fig. 8.10  $V_{th} - T_a$**



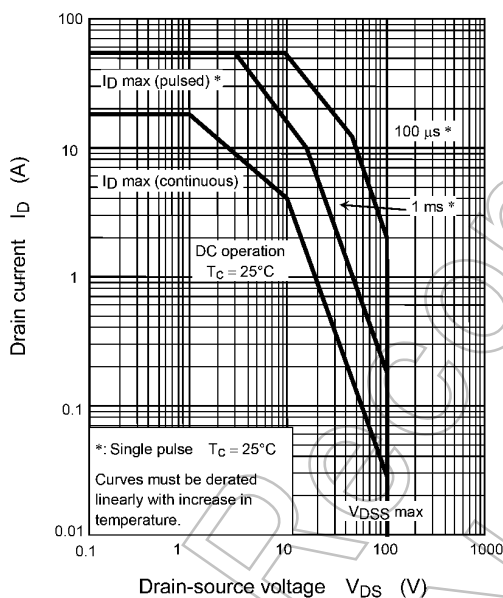
**Fig. 8.11  $P_D - T_c$   
(Guaranteed Maximum)**



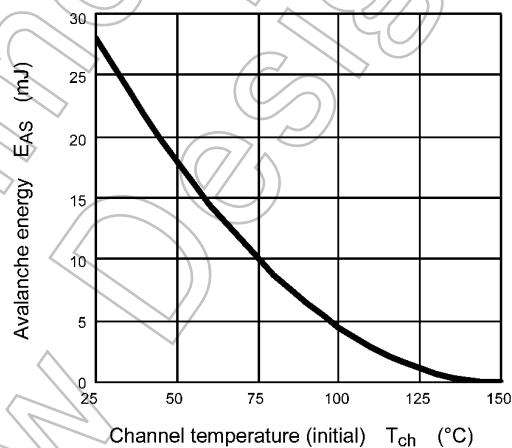
**Fig. 8.12 Dynamic Input/Output Characteristics**



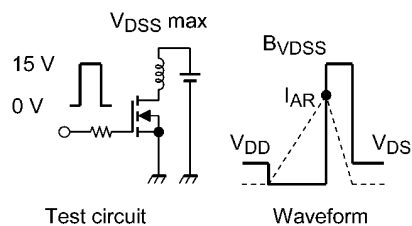
**Fig. 8.13  $r_{th}/R_{th(ch-c)} - t_w$**   
(Guaranteed Maximum)



**Fig. 8.14 Safe Operating Area**  
(Guaranteed Maximum)



**Fig. 8.15  $E_{AS} - T_{ch}$**   
(Guaranteed Maximum)



$$R_G = 25 \, \Omega$$

$$V_{DD} = 25 \, \text{V}, I_{AR} = 18 \, \text{A}$$

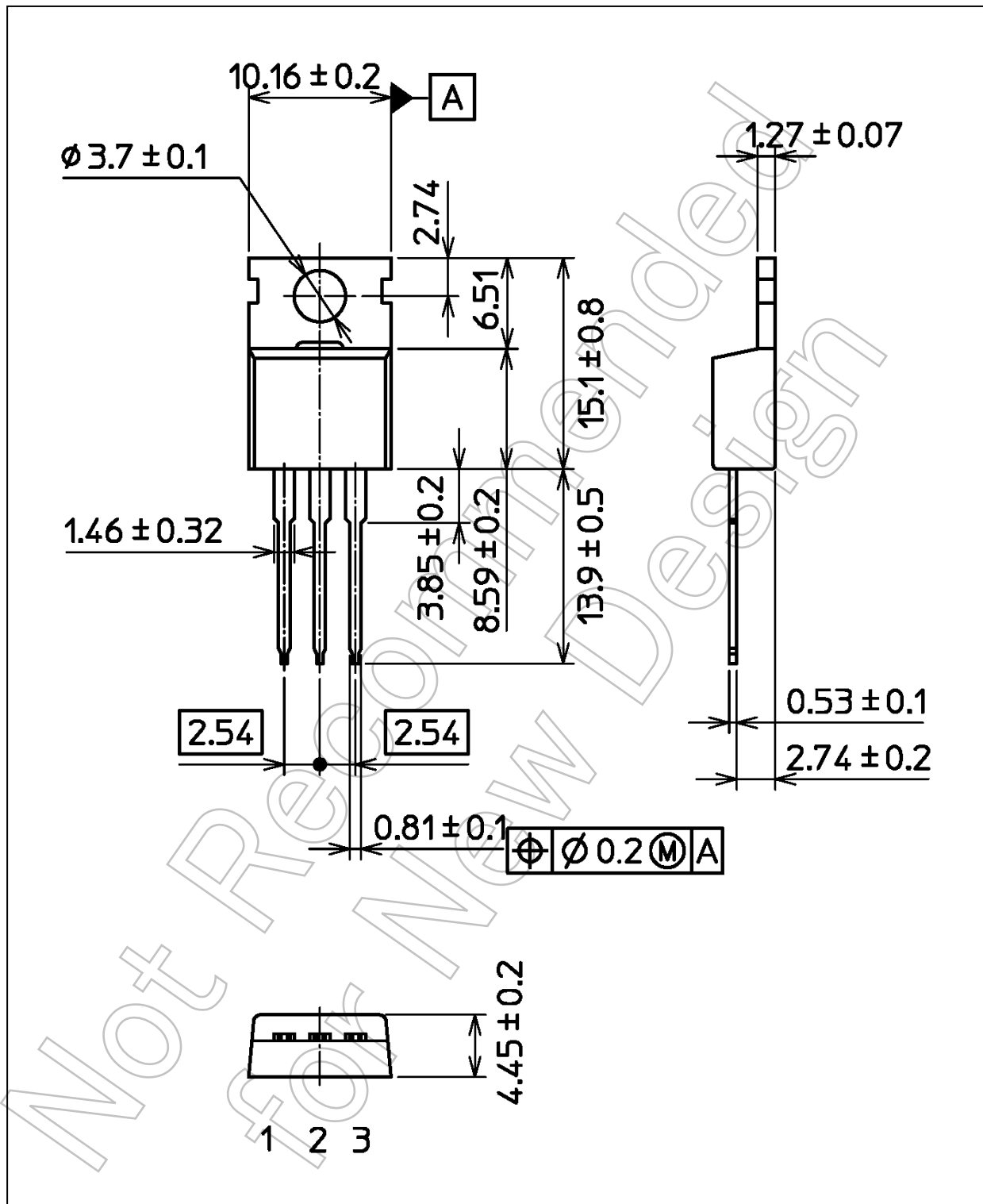
$$E_{AS} = \frac{1}{2} \cdot L \cdot I_{AR}^2 \cdot \left( \frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

**Fig. 8.16 Test Circuit/Waveform**

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

## Package Dimensions

Unit: mm



Weight: 1.93 g (typ.)

Package Name(s)
TOSHIBA: 2-10X1A
Nickname: TO-220



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